

# 10EDA60

## SILICON RECTIFIER DIODE

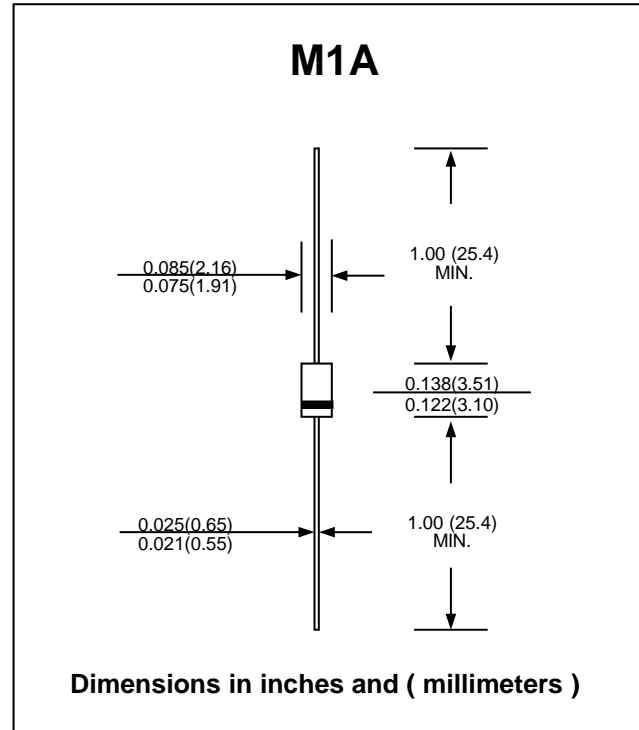
**PRV : 600 Volts**  
**Io : 1.0 Ampere**

### FEATURES :

- \* Glass passivated junction chip
- \* High Surge Capability
- \* Low Forward Voltage drop
- \* Low Reverse Leakage Current
- \* Pb / RoHS Free

### MECHANICAL DATA :

- \* Case : M1A Molded plastic
- \* Epoxy : UL94V-O rate flame retardant
- \* Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
- \* Polarity : Color band denotes cathode end
- \* Mounting position : Any
- \* Weight : 0.20 gram (approximately)



### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

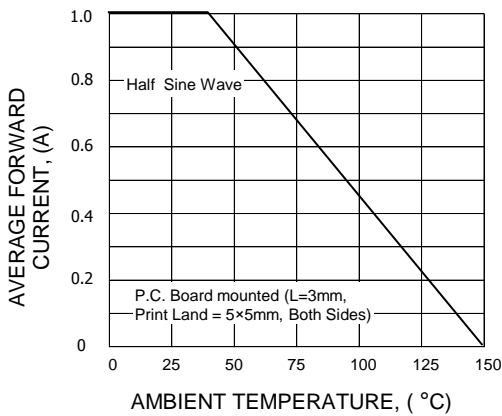
RATING	SYMBOL	VALUE	UNIT
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	600	V
Maximum Average Forward Current 50 Hz Half Sine wave Resistive Load	$I_{F(AV)}$	1.0 <sup>(1)</sup> 0.9 <sup>(2)</sup>	A
Maximum Surge Forward Current, Non-repetitive 50Hz Half Sine Wave, 1cycle	$I_{FSM}$	45	A
Maximum Peak Forward Voltage, $T_j = 25\text{ }^\circ\text{C}$ , $I_{FM} = 1.0\text{A}$	$V_{FM}$	1.0	V
Maximum Peak Reverse Current, $T_j = 25\text{ }^\circ\text{C}$ , $V_{RM} = V_{RRM}$	$I_{RM}$	10	$\mu\text{A}$
Maximum Thermal Resistance Junction to Ambient <sup>(1)</sup>	$R_{\theta JA}$	110	$^\circ\text{C/W}$
Operating Junction Temperature Range	$T_j$	- 40 to + 150	$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	- 40 to + 150	$^\circ\text{C}$

#### Notes :

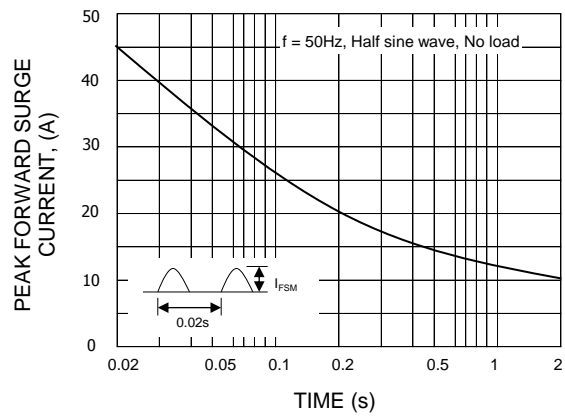
- (1) P.C. Board mounted (L = 3 mm, Print Land = 5 × 5 mm, Both Sides)
- (2) Without Fin or P.C. Board mounted.

## RATING AND CHARACTERISTIC CURVES ( 10EDA60 )

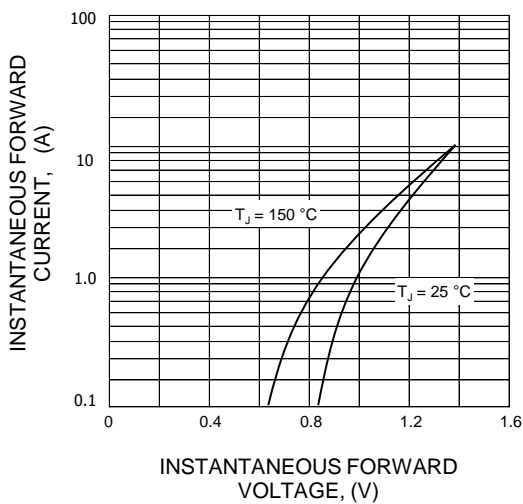
**FIG.1 - AVERAGE FORWARD CURRENT VS. AMBIENT TEMPERATURE**



**FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT**



**FIG.3 - TYPICAL FORWARD CHARACTERISTICS**



**FIG.4 - AVERAGE FORWARD POWER DISSIPATION**

